

NSM6056MT1G

NPN Transistor with Zener Diode

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Driving Circuit
- Switching Applications

MAXIMUM RATINGS – NPN TRANSISTOR

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	40	V
Collector – Base Voltage	V_{CBO}	60	V
Emitter – Base Voltage	V_{EBO}	6.0	V
Collector Current – Continuous	I_C	600	mA
Collector Current – Peak	I_{CM}	900	mA

MAXIMUM RATINGS – ZENER DIODE

Rating	Symbol	Value	Unit
Forward Voltage @ $I_F = 10$ mA	V_F	0.9	V

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) @ $T_A = 25^\circ\text{C}$	P_D	380	mW
Thermal Resistance from Junction-to-Ambient	$R_{\theta JA}$	328	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

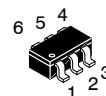
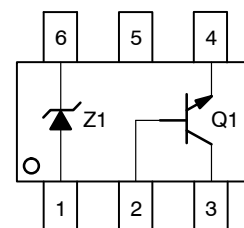
1. FR-4 Minimum Pad.



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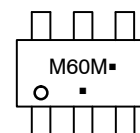
<http://onsemi.com>

NPN Transistor with Zener Diode



SC-74
CASE 318F

MARKING DIAGRAM



M60 = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NSM6056MT1G	SC-74 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NSM6056MT1G

NPN TRANSISTOR – ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (Note 3) (I _C = 1.0 mA _{dc} , I _B = 0)	V _{(BR)CEO}	40	–	Vdc
Collector – Base Breakdown Voltage (I _C = 0.1 mA _{dc} , I _E = 0)	V _{(BR)CBO}	60	–	Vdc
Emitter – Base Breakdown Voltage (I _E = 0.1 mA _{dc} , I _C = 0)	V _{(BR)EBO}	6.0	–	Vdc
Base Cutoff Current (V _{CE} = 35 Vdc, V _{EB} = 0.4 Vdc)	I _{BEV}	–	0.1	μA _{dc}
Collector Cutoff Current (V _{CE} = 35 Vdc, V _{EB} = 0.4 Vdc)	I _{CEX}	–	0.1	μA _{dc}

ON CHARACTERISTICS (Note 3)

DC Current Gain (I _C = 0.1 mA _{dc} , V _{CE} = 1.0 Vdc) (I _C = 1.0 mA _{dc} , V _{CE} = 1.0 Vdc) (I _C = 10 mA _{dc} , V _{CE} = 1.0 Vdc) (I _C = 150 mA _{dc} , V _{CE} = 1.0 Vdc) (I _C = 500 mA _{dc} , V _{CE} = 2.0 Vdc)	h _{FE}	20 40 80 100 40	– – – 300 –	–
Collector – Emitter Saturation Voltage (I _C = 150 mA _{dc} , I _B = 15 mA _{dc}) (I _C = 500 mA _{dc} , I _B = 50 mA _{dc})	V _{CE(sat)}	– –	0.4 0.75	Vdc
Base – Emitter Saturation Voltage (I _C = 150 mA _{dc} , I _B = 15 mA _{dc}) (I _C = 500 mA _{dc} , I _B = 50 mA _{dc})	V _{BE(sat)}	0.75 –	0.95 1.2	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product (I _C = 20 mA _{dc} , V _{CE} = 10 Vdc, f = 100 MHz)	f _T	250	–	MHz
Collector – Base Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)	C _{cb}	–	6.5	pF
Emitter – Base Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{eb}	–	30	pF
Input Impedance (I _C = 1.0 mA _{dc} , V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{ie}	1.0	15	kΩ
Voltage Feedback Ratio (I _C = 1.0 mA _{dc} , V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{re}	0.1	8.0	X 10 ⁻⁴
Small – Signal Current Gain (I _C = 1.0 mA _{dc} , V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	40	500	–
Output Admittance (I _C = 1.0 mA _{dc} , V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{oe}	1.0	30	μmhos

SWITCHING CHARACTERISTICS

Delay Time	(V _{CC} = 30 Vdc, V _{EB} = 2.0 Vdc, I _C = 150 mA _{dc} , I _{B1} = 15 mA _{dc})	t _d	–	15	ns
Rise Time		t _r	–	20	
Storage Time	(V _{CC} = 30 Vdc, I _C = 150 mA _{dc} , I _{B1} = I _{B2} = 15 mA _{dc})	t _s	–	225	ns
Fall Time		t _f	–	30	

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

ZENER DIODE – ELECTRICAL CHARACTERISTICS (V_F = 0.9 Max @ I_F = 10 mA for all types)

Device	Test Current I _{zt} mA	Zener Voltage V _Z		Z _{ZK} I _Z = 0.5 mA Ω Max	Z _{ZT} I _Z = I _{ZT} @ 10% Mod Ω Max	Max IR @ V _R		dV _Z /dt (mV/k) @ I _{ZT1} = 5 mA		C pF Max @ V _R = 0 f = 1 MHz
		Min	Max			μA	V	Min	Max	
NSM6056MT1G	5.0	5.49	5.73	200	40	1.0	2.0	-2.0	2.5	200

NSM6056MT1G

TYPICAL ELECTRICAL CHARACTERISTICS – NPN TRANSISTOR

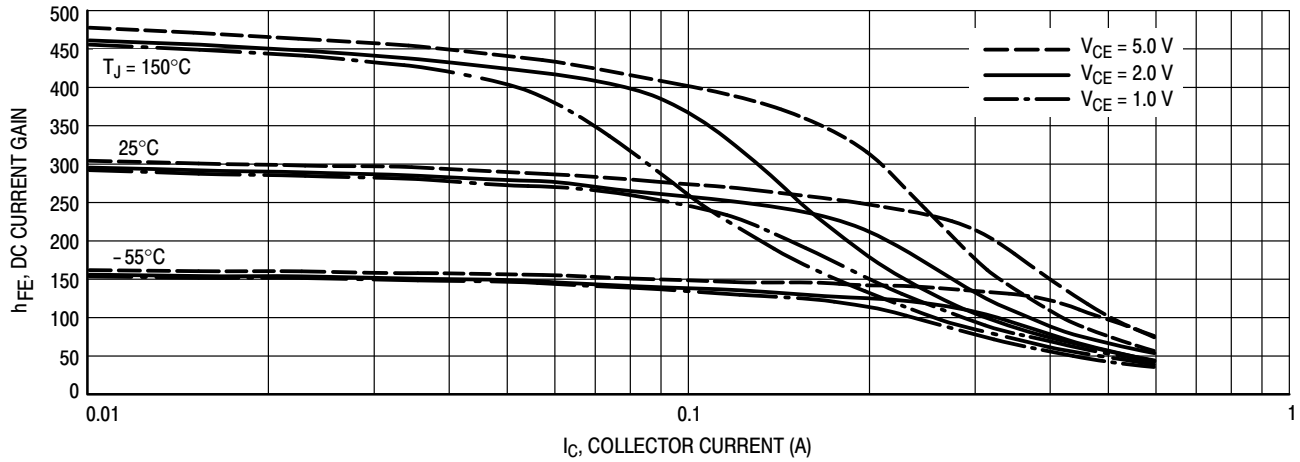


Figure 1. DC Current Gain

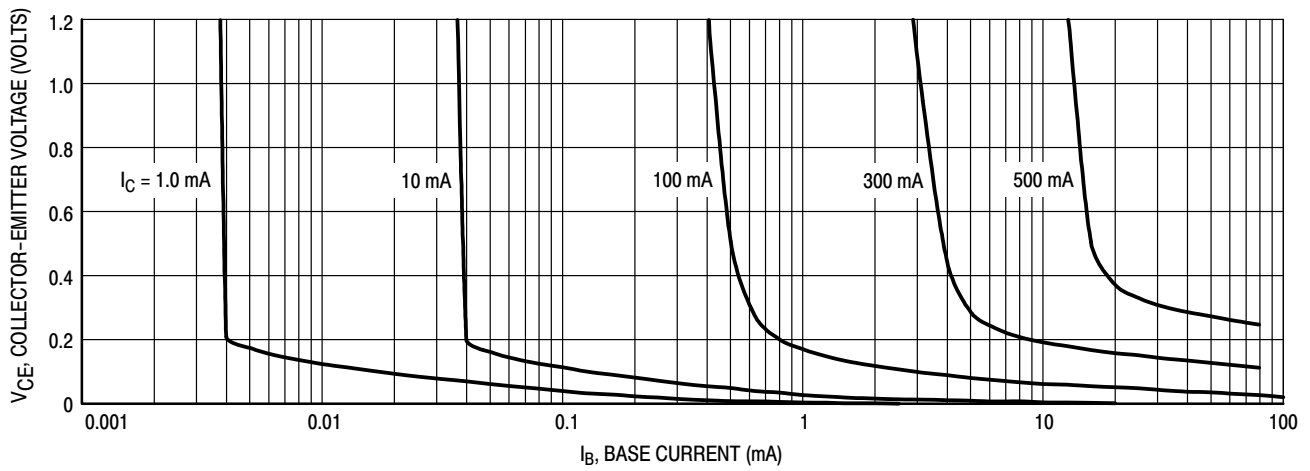


Figure 2. Collector Saturation Region

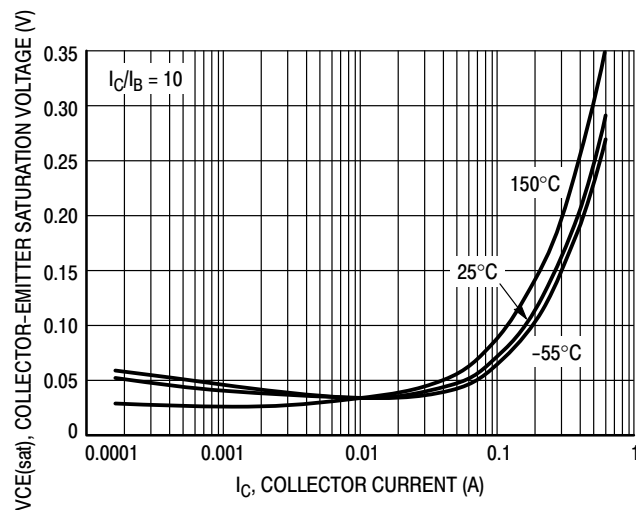


Figure 3. Collector-Emitter Saturation Voltage vs. Collector Current

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TYPICAL ELECTRICAL CHARACTERISTICS - NPN TRANSISTOR

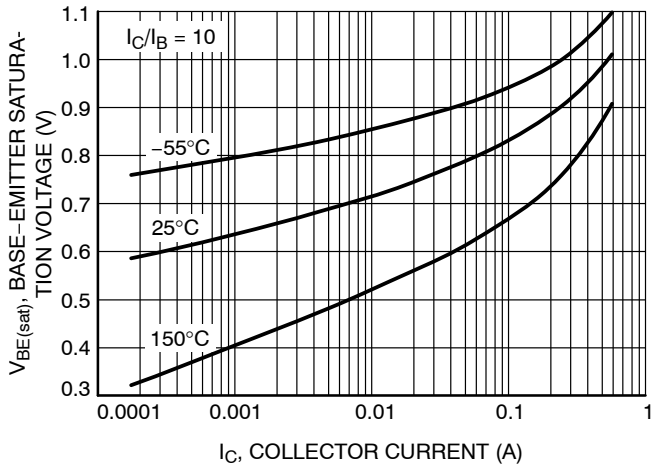


Figure 4. Base-Emitter Saturation Voltage vs. Collector Current

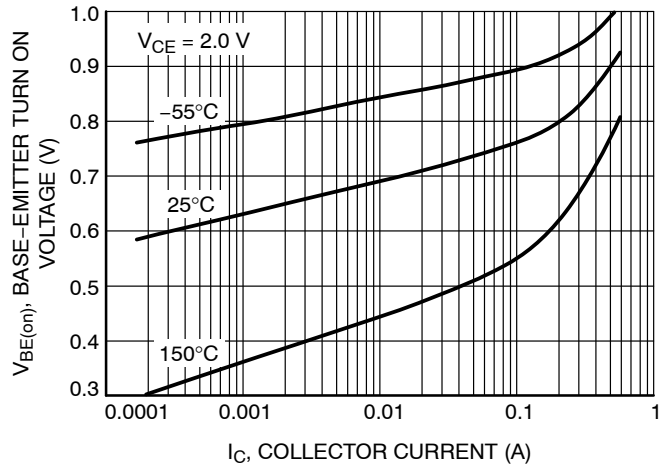


Figure 5. Base-Emitter Turn On Voltage vs. Collector Current

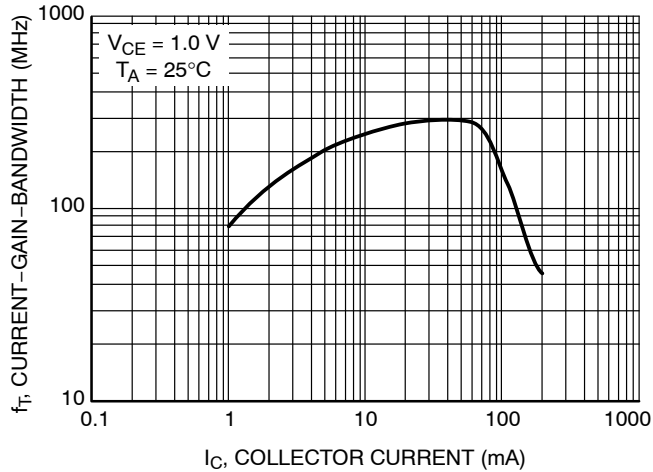


Figure 6. Current-Gain-Bandwidth Product

TYPICAL ELECTRICAL CHARACTERISTICS - ZENER DIODE

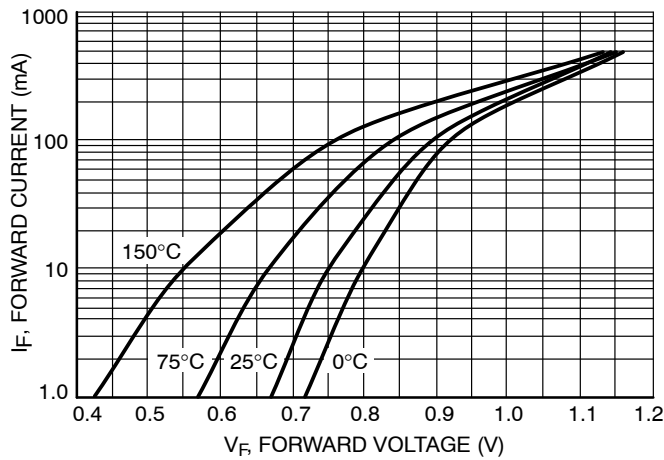


Figure 7. Typical Forward Voltage

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SC-74

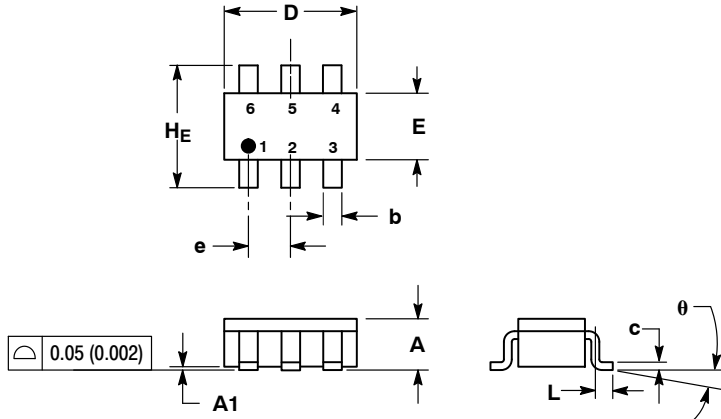
CASE 318F-05

ISSUE N

DATE 08 JUN 2012



SCALE 2:1

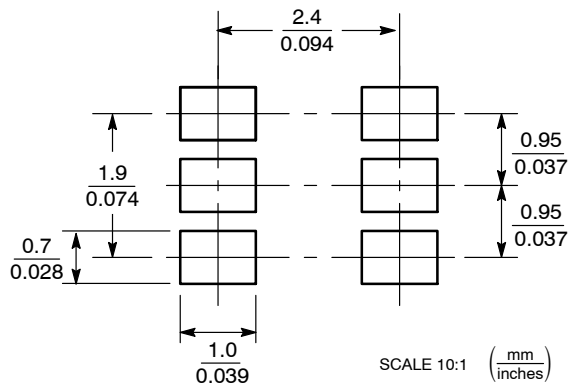


NOTES:

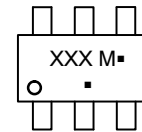
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	-	10°	0°	-	10°

SOLDERING FOOTPRINT*



GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- | | | | | | |
|--|---|--|---|--|--|
| <p>STYLE 1:</p> <p>PIN 1. CATHODE</p> <p>2. ANODE</p> <p>3. CATHODE</p> <p>4. CATHODE</p> <p>5. ANODE</p> <p>6. CATHODE</p> | <p>STYLE 2:</p> <p>PIN 1. NO CONNECTION</p> <p>2. COLLECTOR</p> <p>3. EMITTER</p> <p>4. NO CONNECTION</p> <p>5. COLLECTOR</p> <p>6. BASE</p> | <p>STYLE 3:</p> <p>PIN 1. EMITTER 1</p> <p>2. BASE 1</p> <p>3. COLLECTOR 2</p> <p>4. EMITTER 2</p> <p>5. BASE 2</p> <p>6. COLLECTOR 1</p> | <p>STYLE 4:</p> <p>PIN 1. COLLECTOR 2</p> <p>2. EMITTER 1/EMITTER 2</p> <p>3. COLLECTOR 1</p> <p>4. EMITTER 3</p> <p>5. BASE 1/BASE 2/COLLECTOR 3</p> <p>6. BASE 3</p> | <p>STYLE 5:</p> <p>PIN 1. CHANNEL 1</p> <p>2. ANODE</p> <p>3. CHANNEL 2</p> <p>4. CHANNEL 3</p> <p>5. CATHODE</p> <p>6. CHANNEL 4</p> | <p>STYLE 6:</p> <p>PIN 1. CATHODE</p> <p>2. ANODE</p> <p>3. CATHODE</p> <p>4. CATHODE</p> <p>5. CATHODE</p> <p>6. CATHODE</p> |
| <p>STYLE 7:</p> <p>PIN 1. SOURCE 1</p> <p>2. GATE 1</p> <p>3. DRAIN 2</p> <p>4. SOURCE 2</p> <p>5. GATE 2</p> <p>6. DRAIN 1</p> | <p>STYLE 8:</p> <p>PIN 1. EMITTER 1</p> <p>2. BASE 2</p> <p>3. COLLECTOR 2</p> <p>4. EMITTER 2</p> <p>5. BASE 1</p> <p>6. COLLECTOR 1</p> | <p>STYLE 9:</p> <p>PIN 1. EMITTER 2</p> <p>2. BASE 2</p> <p>3. COLLECTOR 1</p> <p>4. EMITTER 1</p> <p>5. BASE 1</p> <p>6. COLLECTOR 2</p> | <p>STYLE 10:</p> <p>PIN 1. ANODE/CATHODE</p> <p>2. BASE</p> <p>3. EMITTER</p> <p>4. COLLECTOR</p> <p>5. ANODE</p> <p>6. CATHODE</p> | <p>STYLE 11:</p> <p>PIN 1. EMITTER</p> <p>2. BASE</p> <p>3. ANODE/CATHODE</p> <p>4. ANODE</p> <p>5. CATHODE</p> <p>6. COLLECTOR</p> | |

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